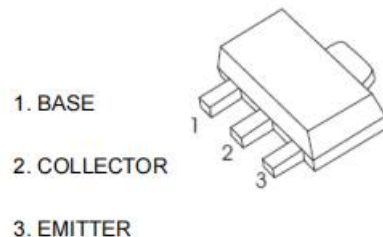


SOT-89 Bipolar Transistor 双极型三极管

■ Features 特点

NPN Switching 开关



■ Absolute Maximum Ratings 最大额定值

Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Collector-Base Voltage 集电极基极电压	V_{CB0}	75	V
Collector-Emitter Voltage 集电极发射极电压	V_{CEO}	40	V
Emitter-Base Voltage 发射极基极电压	V_{EBO}	6	V
Collector Current 集电极电流	I_C	600	mA
Power dissipation 耗散功率	$P_C(T_a=25^\circ\text{C})$	500	mW
Thermal Resistance Junction-Ambient 热阻	$R_{\theta JA}$	250	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature 结温和储藏温度	T_J, T_{stg}	-55to+150 $^\circ\text{C}$	

■ Device Marking 产品打标

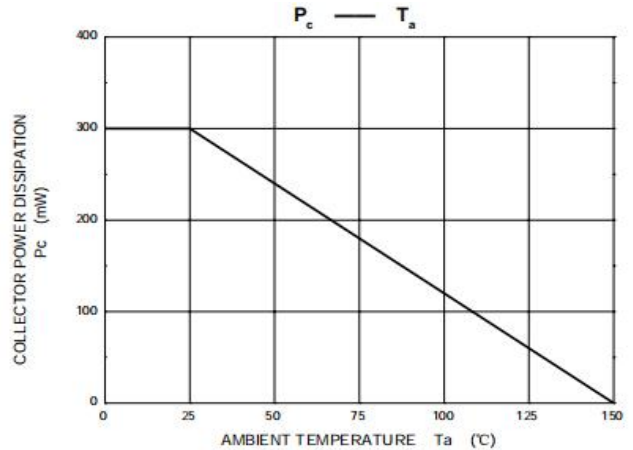
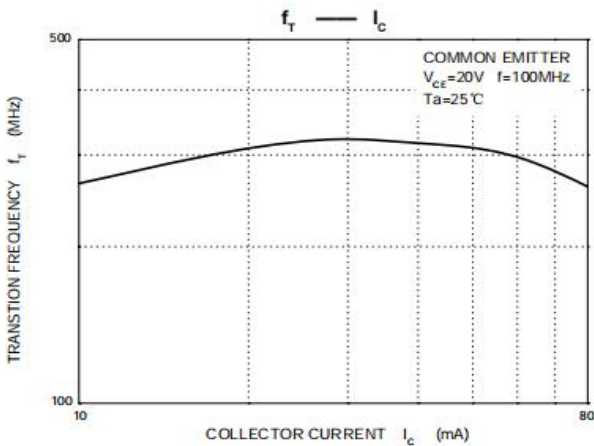
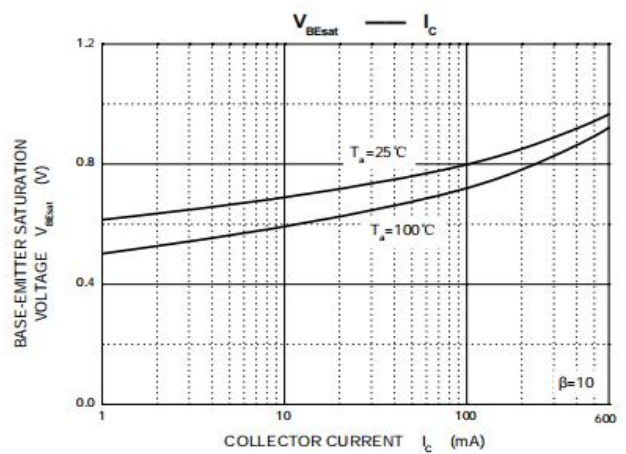
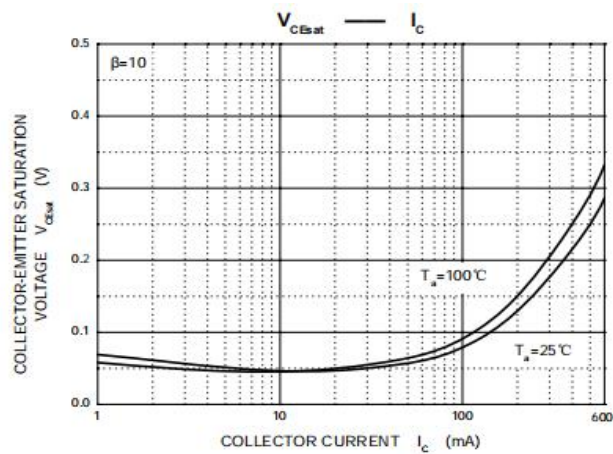
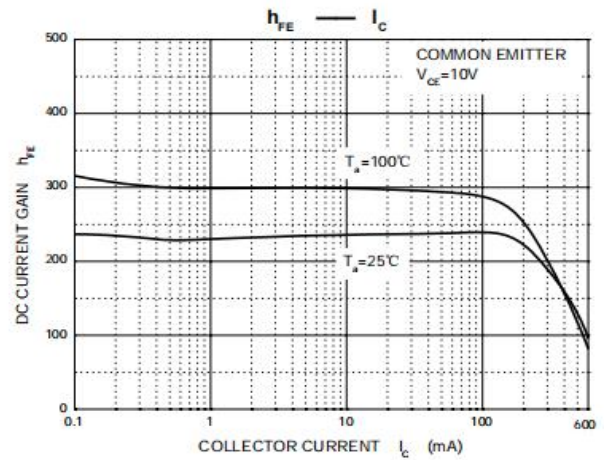
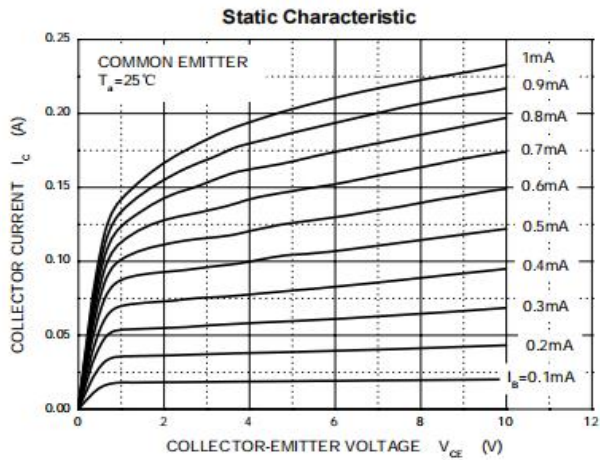
PXT2222A=1P

■ Electrical Characteristics 电特性

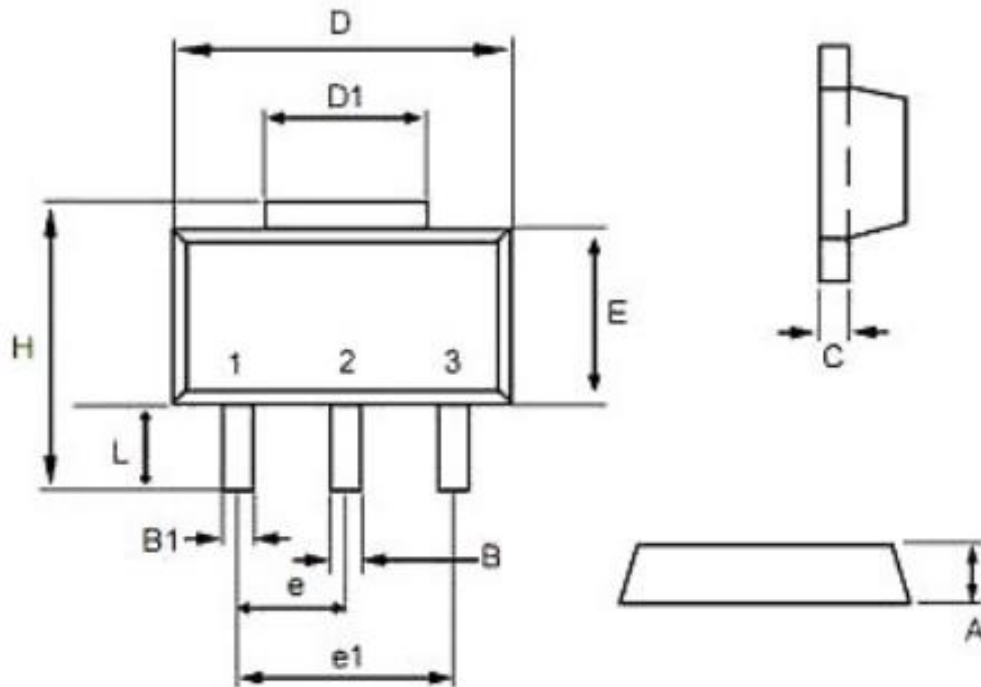
($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Min 最小值	Type 典型值	Max 最大值	Unit 单位
Collector-Base Breakdown Voltage 集电极基极击穿电压($I_C=1\text{mA}$, $I_E=0$)	BV_{CBO}	75	—	—	V
Collector-Emitter Breakdown Voltage 集电极发射极击穿电压($I_C=10\text{mA}$, $I_B=0$)	BV_{CEO}	40	—	—	V
Emitter-Base Breakdown Voltage 发射极基极击穿电压($I_E=1\text{mA}$, $I_C=0$)	BV_{EBO}	6	—	—	V
Collector-Base Leakage Current 集电极基极漏电流($V_{CB}=50\text{V}$, $I_E=0$)	I_{CBO}	—	—	100	nA
Collector-Emitter Leakage Current 集电极发射极漏电流($V_{CE}=30\text{V}$, $V_{BE}=-0.5\text{V}$)	I_{CEX}	—	—	100	nA
Emitter-Base Leakage Current 发射极基极漏电流($V_{EB}=4\text{V}$, $I_C=0$)	I_{EBO}	—	—	100	nA
DC Current Gain($V_{CE}=10\text{V}$, $I_C=0.1\text{mA}$) 直流电流增益($V_{CE}=10\text{V}$, $I_C=150\text{mA}$) ($V_{CE}=10\text{V}$, $I_C=500\text{mA}$)	H_{FE}	35 100 40	—	300	
Collector-Emitter Saturation Voltage 集电极发射极饱和压降($I_C=500\text{mA}$, $I_B=50\text{mA}$) ($I_C=150\text{mA}$, $I_B=15\text{mA}$)	$V_{CE(sat)}$	—	—	0.6 0.4	V
Base-Emitter Saturation Voltage 基极发射极饱和压降($I_C=500\text{mA}$, $I_B=50\text{mA}$) ($I_C=150\text{mA}$, $I_B=15\text{mA}$)	$V_{BE(sat)}$	—	—	2 1.2	V
Transition Frequency 特征频率($V_{CE}=20\text{V}$, $I_C=20\text{mA}$)	f_T	300	—	—	MHz
Delay Time 延迟时间 ($V_{CC}=30\text{V}$, $V_{BE}=-0.5\text{V}$, $I_C=150\text{mA}$, $I_{B1}=15\text{mA}$)	t_d	—	—	10	ns
Rise Time 上升时间 ($V_{CC}=30\text{V}$, $V_{BE}=-0.5\text{V}$, $I_C=150\text{mA}$, $I_{B1}=15\text{mA}$)	t_r	—	—	25	ns
Storage Time 贮存时间 ($V_{CC}=30\text{V}$, $I_C=150\text{mA}$, $I_{B1}=I_{B2}=15\text{mA}$)	t_s	—	—	225	ns
Fall Time 下降时间 ($V_{CC}=30\text{V}$, $I_C=150\text{mA}$, $I_{B1}=I_{B2}=15\text{mA}$)	t_f	—	—	60	ns

■ Typical Characteristic Curve 典型特性曲线



■Dimension 外形封装尺寸



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.40	1.60	0.055	0.063
B	0.40	0.56	0.016	0.022
B1	0.35	0.48	0.014	0.019
C	0.35	0.44	0.014	0.017
D	4.40	4.60	0.173	0.181
D1	1.35	1.83	0.053	0.072
e	1.45	1.55	0.057	0.061
e1	2.95	3.05	0.116	0.120
E	2.29	2.60	0.090	0.102
H	3.75	4.25	0.148	0.167
L	0.80	1.20	0.031	0.047